

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	0	bedell near steven .in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	46	cohen near guy.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	0	bedell near steven.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	13	chen near huajie.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L8	16	(soi) near25 (amorphiz\$4)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
10	BRS	L10	15	((soi) near25 (amorph\$6)) near25 (defect\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
11	BRS	L11	46	((soi) near25 (amorph\$6)) near25 (anneal\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
12	BRS	L12	0	((semiconductor-on- insulator) near25 (amorph\$6)) near25 (anneal\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
17	BRS	L16	62	(ge-containing) near15 (si-containing)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
18	BRS	L18	56081	(ge or germanium) near15 (si or silicon)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
19	BRS	L19	943	(ge or germanium) near15 (si or silicon) near25 (soi)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
20	BRS	L20	66	(ge or germanium) near15 (si or silicon) near25 (soi) near15 (amorph\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
25	BRS	L25	0	(ge or germanium) near3 (strain\$3) near15 (amorphi\$5)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	U	1	Document ID	Title
1			US 20040235264 A1	Gettering of silicon on insulator using relaxed silicon germanium epitaxial proximity layers
2			US 20040142541 A1	STRAINED SILICON-ON-INSULATOR (SSOI) AND METHOD TO FORM THE SAME
3			US 20040129975 A1	Semiconductor device and method for manufacturing the same
4			US 20030027381 A1	XE preamorphizing implantation
5			US 6825102 B1	Method of improving the quality of defective semiconductor material
6			US 6774015 B1	Strained silicon-on-insulator (SSOI) and method to form the same
7			US 6743689 B1	Method of fabrication SOI devices with accurately defined monocrystalline source/drain extensions

	U	1	Document ID	Title
8			US 6713819 B1	SOI MOSFET having amorphized source drain and method of fabrication
9			US 6696352 B1	Method of manufacture of a multi-layered substrate with a thin single crystalline layer and a versatile sacrificial layer
10			US 6624037 B2	XE preamorphizing implantation
11			US 6429054 B1	Method of fabricating semiconductor-on-insulator (SOI) device with hyperabrupt source/drain junctions

	U	1	Document ID	Title
12			US 6395587 B1	Fully amorphized source/drain for leaky junctions
13			US 6352909 B1	Process for lift-off of a layer from a substrate
14			US 5986311 A	Semiconductor device having recrystallized source/drain regions
15			US 5960268 A	Semiconductor device and method of fabricating the same
16			US 5360752 A	Method to radiation harden the buried oxide in silicon-on-insulator structures